# **BTS6302U**



# Wideband high linearity pre-driver amplifier

Rev. 10 — 19 October 2021

Product data sheet

## 1 General description

The BTS6302U is a wideband, high linearity, pre-driver amplifier for 5G massive MIMO infrastructure applications, with fast on-off switching to support TDD systems. The amplifier is designed to operate between 2.3 GHz and 5 GHz. It is housed in a 3 mm  $\times$  3 mm  $\times$  0.85 mm 16-terminal HVQFN package.

The amplifier is ESD protected on all terminals.

## 2 Features and benefits

- High saturated output power P<sub>o(sat)</sub> = 27.9 dBm
- High power-gain G<sub>p</sub> = 38 dB
- High linearity performance ACLR = -43 dBc
- · Unconditionally stable
- · Fast switching to support TDD systems
- 5 V single supply, quiescent current 68 mA
- Small 16-terminal leadless package 3 mm x 3 mm x 0.85 mm
- ESD protection on all terminals
- · Moisture sensitivity level 1

## 3 Applications

- · Wireless infrastructure 5G NR mMIMO
- · High linearity pre-driver
- · TDD systems



Wideband high linearity pre-driver amplifier

## 4 Quick reference data

#### Table 1. Quick reference data

f = 3.5 GHz;  $V_{CC}$  = 5 V;  $T_{amb}$  = 25 °C; input 100  $\Omega$ , and output 50  $\Omega$ ; unless otherwise specified. Values under Min/Max in boldface font are guaranteed by test; Values in lightface font are based on simulation or characterization.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CC</sub>	supply current	ON state, P <sub>o</sub> = 15 dBm		-	98	120	mA
		ON state, quiescent		-	68	88	mA
		OFF state		-	1	1.5	mA
G <sub>p</sub>	power gain	ON state		35.8	38	40.8	dB
		OFF state		-	-60	-45	dB
P <sub>o(sat)</sub>	saturated output power		[1]	27.7	27.9	-	dBm
ACLR	adjacent channel leakage ratio	CP-OFDM with 100 MHz channel BW, QPSK modulation, and 60 kHz SCS, fully allocated, $P_{\rm o}$ = 15 dBm		-	-43	-40	dBc

<sup>[1]</sup> Connector and Printed-Circuit Board (PCB) losses have been de-embedded, 3 dB gain compression

# 5 Ordering information

#### Table 2. Ordering information

Type number Orderable part		Package	kage				
	number	Name	Description	Version			
BTS6302U	BTS6302UJ	HVQFN16	3 mm × 3 mm × 0.85 mm, 16 terminals no leads	SOT758-1			

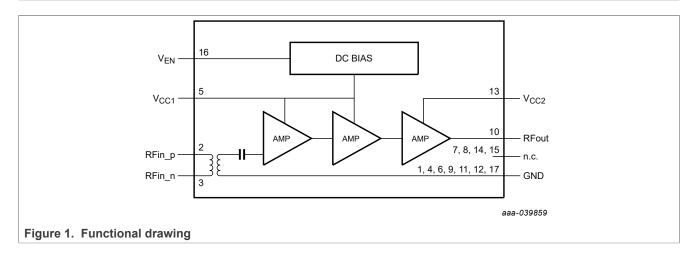
# 6 Marking

## Table 3. Marking

Type number	Marking code
BTS6302U	32U

Wideband high linearity pre-driver amplifier

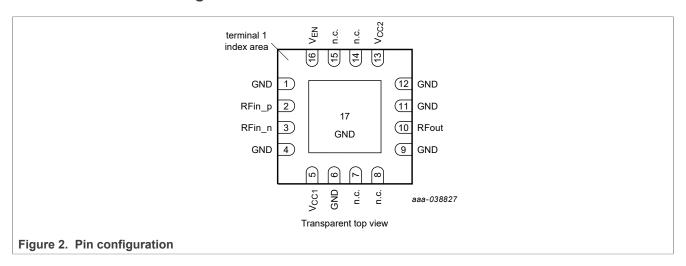
# 7 Functional diagram



Wideband high linearity pre-driver amplifier

# 8 Pinning information

#### 8.1 Pinning



### 8.2 Pin description

Table 4. Pin description

Pin	Symbol	Description
1, 4, 6, 9, 11, 12, and 17	GND	PCB ground
2	RFin_p	RF input
3	RFin_n	RF input
5	V <sub>CC1</sub>	supply voltage
7, 8, 14, and 15	n.c. <sup>[1]</sup>	not connected
10	RFout	RF output
13	VCC2	supply voltage
16	V <sub>EN</sub>	voltage enable; LOW = OFF state; HIGH = ON state

<sup>[1]</sup> n.c. means that pin is not connected inside package, and may be left floating in application

# 9 Functional description

Table 5. Shutdown control

V <sub>en</sub>	voltage applied at pin V <sub>en</sub> [1]	State	Condition
LOW	$0 < V (V_{en}) < V_{IL(max)}$	OFF	bias active, amplifier not active
HIGH	$V_{IH(min)} < V(V_{en}) < V_{I(max)}$	ON	bias active, amplifier active

<sup>[1]</sup>  $V_{EN}$  can only be made HIGH, after supply voltage has been applied to pin  $V_{CC1}$ 

Wideband high linearity pre-driver amplifier

# 10 Limiting values

#### Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.3	6	V
V <sub>EN</sub>	enable voltage		-0.3	4	V
P <sub>i(RF)CW</sub>	continuous waveform RF input power	ON state, OFF state	-	10	dBm
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C
V <sub>ESD</sub>	electrostatic discharge voltage	Human Body Model (HBM) According to ANSI/ESDA/JEDEC standard JS-001	-	+/-2	kV
		Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	-	+/-500	V

# 11 Recommended operating conditions

Table 7. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CC</sub>	supply voltage	[1]	4.75	5	5.25	V
V <sub>IL</sub>	LOW-level input voltage		0	-	0.6	V
V <sub>IH</sub>	HIGH-level input voltage		1.2	-	3.6	V
V <sub>I(max)</sub>	maximum input voltage		-	-	3.6	V
Z <sub>0</sub>	characteristic impedance differential input		-	100	-	Ω
	characteristic impedance output		-	50	-	Ω
T <sub>case</sub>	case temperature		-40	-	115	°C

<sup>[1]</sup> supply voltage at  $V_{\text{CC1}}$  must be applied before, or at the same time as applying supply voltage to pin  $V_{\text{CC2}}$ 

### 12 Thermal characteristics

Table 8. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-case)</sub>	junction to case thermal resistance	[1] [2]	50	K/W

<sup>[1]</sup> Case is ground solder pad.

<sup>[2]</sup> Thermal resistance determined with device mounted, and device bottom case kept at constant temperature.

Wideband high linearity pre-driver amplifier

## 13 Characteristics

#### Table 9. Characteristics

f = 3.5 GHz;  $V_{CC}$  = 5 V;  $T_{amb}$  = 25 °C; input 100  $\Omega$ , and output 50  $\Omega$ ; unless otherwise specified. Values under Min/Max in boldface font are guaranteed by test; Values in lightface font are based on simulation or characterization.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CC</sub>	supply current	ON state, P <sub>o</sub> = 15 dBm		-	98	120	mA
		ON state, quiescent	,	-	68	88	mA
		OFF state		-	1	1.5	mA
Gp	power gain	ON state, t <sub>amb</sub> = -40 °C to 115 °C <sup>[1]</sup>					J
		f = 2.6 GHz		35.7	38	40.6	dB
		f = 3.5 GHz		35.8	38	40.8	dB
		f = 4.2 GHz		33.8	36	38.6	dB
		OFF state		-	-60	-45	dB
G <sub>flat</sub>	gain flatness	f = 2.3 GHz to 2.7 GHz		-	0.9	1	dB
		f = 3.3 GHz to 3.8 GHz		-	1	1.1	dB
		f = 3.8 GHz to 4.2 GHz		-	1.2	1.3	dB
t <sub>d(grp)</sub>	group delay	f = 2.3 GHz to 2.7 GHz		-	0.4	0.5	ns
	time	f = 3.3 GHz to 3.8 GHz		-	0.4	0.5	ns
		f = 3.8 GHz to 4.2 GHz		-	0.4	0.5	ns
P <sub>o(sat)</sub>	saturated output power	f = 2.6 GHz	[2]	28.1	28.3	-	dBm
		f = 3.5 GHz	[2]	27.7	27.9	-	dBm
		f = 4.2 GHz	[2]	26.5	26.7	-	dBm
P <sub>L(1dB)</sub>	output power	f = 2.6 GHz		27.8	28.1	-	dBm
	at1 dB gain compression	f = 3.5 GHz	,	27.3	27.6	-	dBm
		f = 4.2 GHz		26	26.3	-	dBm
IP3 <sub>o</sub>	output third- order intercept point	2-tone; tone spacing = 100 MHz; P <sub>o</sub> = 15 dBm		27	33	-	dBm
CMRR	common mode rejection ratio			22	24	-	dB
RLi	input return loss	f = 2.6 GHz		18	20	-	dB
		f = 3.5 GHz		9.5	10	-	dB
		f = 4.2 GHz		11	12	-	dB
RLo	output return	f = 2.6 GHz	,	10	11	-	dB
	loss	f = 3.5 GHz	,	10	11	-	dB
		f = 4.2 GHz		10	12	-	dB
ISL <sub>r</sub>	reverse isolation			63	65	-	dB

#### Wideband high linearity pre-driver amplifier

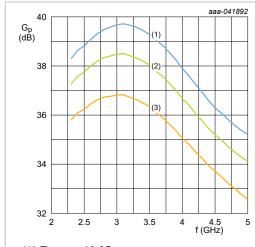
Table 9. Characteristics...continued

f = 3.5 GHz;  $V_{CC}$  = 5 V;  $T_{amb}$  = 25 °C; input 100  $\Omega$ , and output 50  $\Omega$ ; unless otherwise specified. Values under Min/Max in boldface font are guaranteed by test; Values in lightface font are based on simulation or characterization.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
NF	noise figure	f = 2.6 GHz	[3]	-	3.1	3.2	dB
		f = 3.5 GHz	[3]	-	3.4	3.5	dB
		f = 4.2 GHz	[3]	_	3.7	3.8	dB
t <sub>s(pon)</sub>	power-on settling time	V <sub>EN</sub> from LOW to HIGH to gain settled within 0.1 dB of final value and phase settled to within 1 degree of final value		-	0.8	0.9	μs
t <sub>s(poff)</sub>	power-off settling time	$V_{\text{EN}}$ from HIGH to LOW to gain settled to be < 5 $\%$ of gain in ON state		-	0.05	0.1	μs
К	Rollett stability factor	1 MHz to 15 GHz		5	-	-	
ACLR	adjacent channel leakage ratio	CP-OFDM with 100 MHz channel BW, QPSK modulation, and 60 kHz SCS, fully allocated, $P_{\rm o}$ = 15 dBm		-	-43	-40	dBc

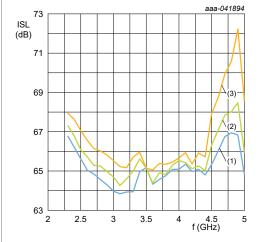
- These values are guaranteed by final test at t<sub>amb</sub>
- Connector and Printed-Circuit Board (PCB) losses have been de-embedded, 3 dB gain compression Connector and Printed-Circuit Board (PCB) losses have been de-embedded

# 14 Graphs



- (1) T<sub>amb</sub> = -40 °C
- (2) T<sub>amb</sub> = 25 °C
- (3) T<sub>amb</sub> = 115 °C

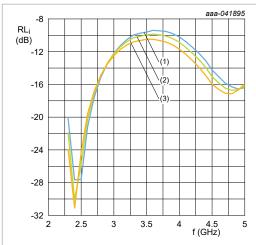
Figure 3. G<sub>p</sub> versus frequency over temperature



- (1) T<sub>amb</sub> = -40 °C
- (2) T<sub>amb</sub> = 25 °C
- (3) T<sub>amb</sub> = 115 °C

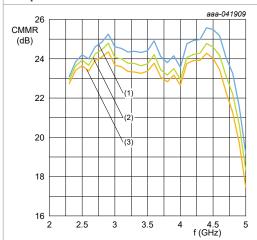
Figure 4. ISL<sub>r</sub> versus frequency over temperature

### Wideband high linearity pre-driver amplifier



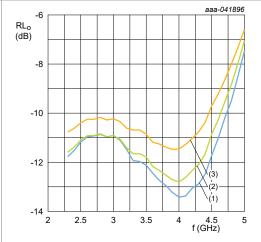
- (1) T<sub>amb</sub> = -40 °C
- (2) T<sub>amb</sub> = 25 °C
- (3) T<sub>amb</sub> = 115 °C

Figure 5. RL<sub>i</sub> S11 versus frequency over temperature



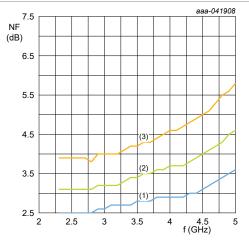
- (1) T<sub>amb</sub> = -40 °C
- (2) T<sub>amb</sub> = 25 °C
- (3) T<sub>amb</sub> = 115 °C

Figure 7. CMMR versus frequency over temperature



- (1) T<sub>amb</sub> = -40 °C
- (2) T<sub>amb</sub> = 25 °C
- (3) T<sub>amb</sub> = 115 °C

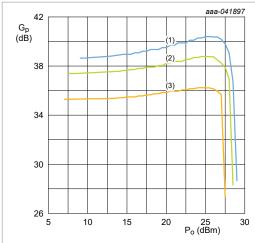
Figure 6. RL<sub>o</sub> S22 versus frequency over temperature



- (1) T<sub>amb</sub> = -40 °C
- (2) T<sub>amb</sub> = 25 °C
- (3) T<sub>amb</sub> = 115 °C

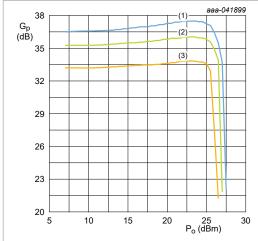
Figure 8. NF versus frequency over temperature

### Wideband high linearity pre-driver amplifier



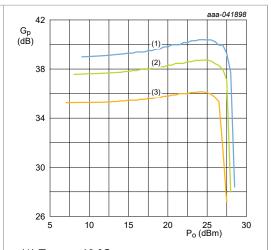
- (1) T<sub>amb</sub> = -40 °C
- (2) T<sub>amb</sub> = 25 °C
- (3) T<sub>amb</sub> = 115 °C

Figure 9.  $G_p$  versus  $P_o$  at 2.6 GHz over temperature



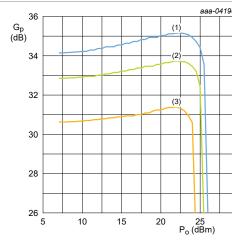
- (1) T<sub>amb</sub> = -40 °C
- (2) T<sub>amb</sub> = 25 °C
- (3) T<sub>amb</sub> = 115 °C

Figure 11.  $G_p$  versus  $P_0$  at 4.2 GHz over temperature



- (1) T<sub>amb</sub> = -40 °C
- (2) T<sub>amb</sub> = 25 °C
- (3) T<sub>amb</sub> = 115 °C

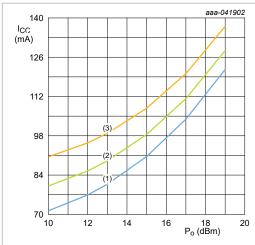
Figure 10.  $G_p$  versus  $P_o$  at 3.5 GHz over temperature



- (1) T<sub>amb</sub> = -40 °C
- (2) T<sub>amb</sub> = 25 °C
- (3) T<sub>amb</sub> = 115 °C

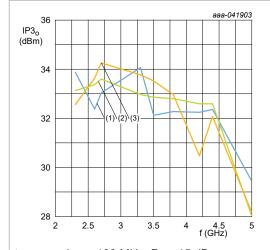
Figure 12.  $G_p$  versus  $P_0$  at 5 GHz over temperature

#### Wideband high linearity pre-driver amplifier



- (1) T<sub>amb</sub> = -40 °C
- (2) T<sub>amb</sub> = 25 °C
- (3) T<sub>amb</sub> = 115 °C

Figure 13.  $I_{CC}$  versus  $P_o$  at 3.5 GHz over temperature

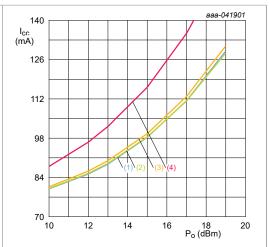


tone spacing = 100 MHz,  $P_o$  = 15 dBm,

 $V_{CC} = 5 V$ 

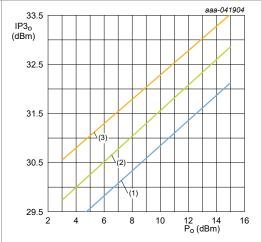
- (1) T<sub>amb</sub> = -40 °C
- (2) T<sub>amb</sub> = 25 °C
- (3) T<sub>amb</sub> = 115 °C

Figure 15. IP3<sub>o</sub> versus frequency over temperature



- (1) f = 2.6 GHz
- (2) f = 3.5 GHz
- (3) f = 4.2 GHz
- (4) f = 5 GHz

Figure 14.  $I_{CC}$  versus  $P_0$  over frequency at 25 °C

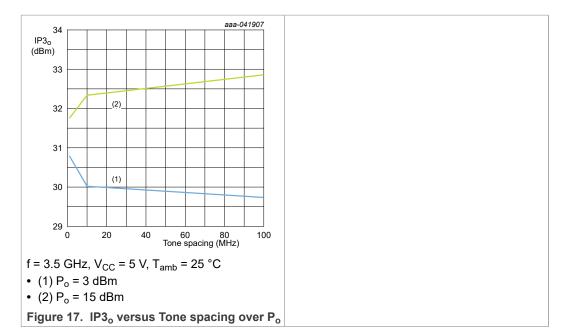


tone spacing = 100 MHz,  $V_{CC}$  = 5 V

- (1) T<sub>amb</sub> = -40 °C
- (2) T<sub>amb</sub> = 25 °C
- (3) T<sub>amb</sub> = 115 °C

Figure 16. IP3<sub>o</sub> versus P<sub>o</sub> over temperature

### Wideband high linearity pre-driver amplifier



Wideband high linearity pre-driver amplifier

# 15 Application information

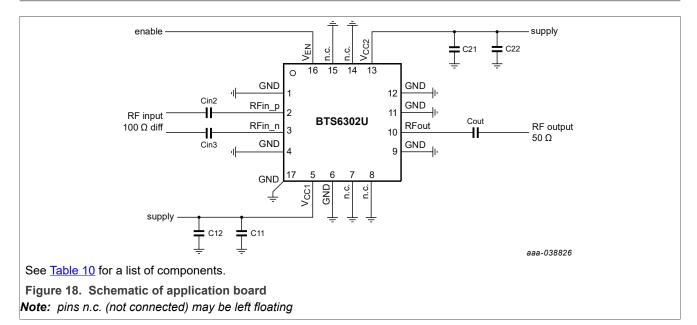


Table 10. List of components

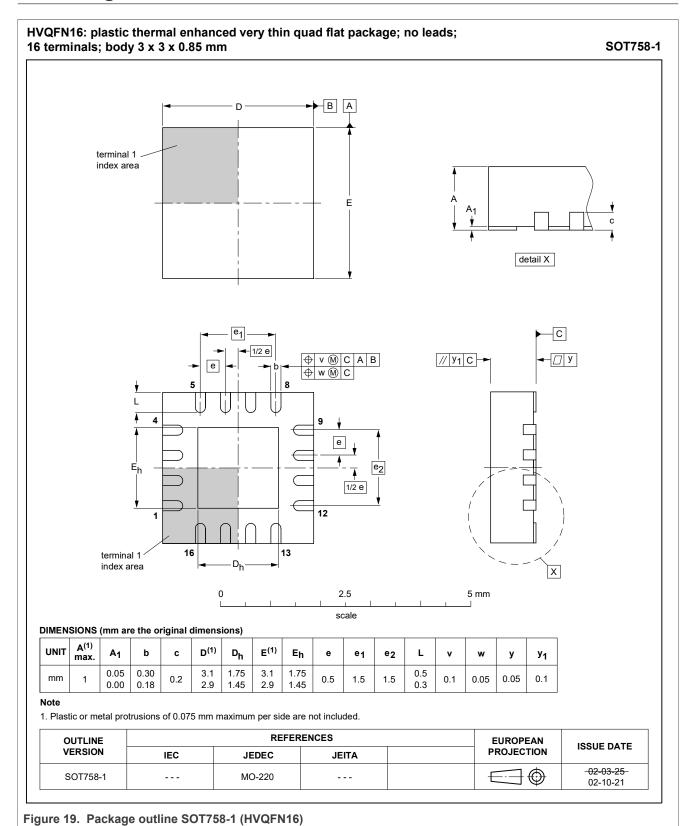
See Figure 18 for schematics.

Component	Description	Value	Remarks
Cin2, and Cin3	capacitor	18 pF	in a 50 Ω PCB track
C <sub>out</sub>	capacitor	3.9 pF	in a 50 Ω PCB track
C11, and C21	capacitor	10 nF	recommended
C12, and C22 [1]	capacitor	1 µF	

[1] placement of C12 and C22 is optional

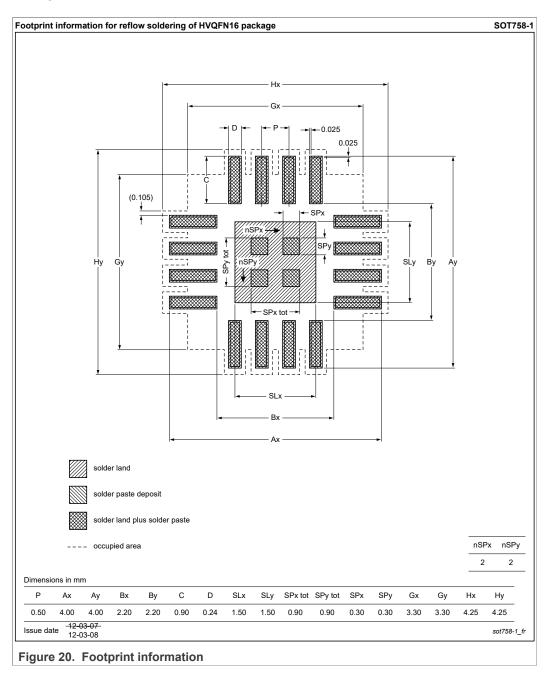
Wideband high linearity pre-driver amplifier

# 16 Package outline



Wideband high linearity pre-driver amplifier

## 16.1 Footprint and solder information



# 17 Handling information

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

BTS6302U

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Wideband high linearity pre-driver amplifier

## 18 Abbreviations

#### Table 11. Abbreviations

Acronym	Description
5G NR	5 <sup>th</sup> generation new radio
ACLR	adjacent channel leakage ratio
CP-OFDM	cyclic prefix orthogonal frequency division multiplexing
CMMR	common mode rejection ratio
ESD	electrostatic discharge
mMIMO	massive multiple-input multiple-output
PA	power amplifier
RF	radio frequency
TDD	time-division duplexing

# 19 Revision history

#### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BTS6302U v.10	20211019	Product data sheet	-	BTS6302U v.9	
modification	<ul> <li>Updated the Application diagram with a ground symbol at pin 15</li> <li>Changed Typical, and Maximum value at t<sub>s(pon)</sub></li> <li>added footnote to G<sub>p</sub> in characteristics table</li> <li>changed status to product data sheet</li> </ul>				
BTS6302U v.9	20210610	Preliminary data sheet	-	BTS6302U v.8	
modification	<ul> <li>corrected label on X-axis, and Y-axis on figure 13, and 16 graphics</li> <li>changed min max values on some parameters</li> </ul>				
BTS6302U v.8	20210423	Preliminary data sheet	-	BTS6302U v.7.1	
modification	<ul> <li>added graphics</li> <li>changed min max values on some parameters</li> <li>changed status from Objective to Preliminary data sheet</li> </ul>				
BTS6302U v.7.1	20210331	Objective data sheet	-	BTS6302U v.6.3	
modification	added Min/Max values to most parameters				
BTS6302U v.6.3	20210319	Objective data sheet	-	BTS6302U v.6.2	
modification	changed remark on C11, and C21 in List of components table to, recommended				
BTS6302U v.6.2	20210318	Objective data sheet	-	BTS6302U v.6.1	
modification	corrected the legend for graphic on NF versus frequency over temperature				
BTS6302U v.6.1	20210317	Objective data sheet	-	BTS6302U v.6	
modification	added graphic on NF versus frequency over temperature				
BTS6302U v.6	20210126	Objective data sheet	-	BTS6302U v.5	
modification	<ul><li>changed Typical values on some parameters</li><li>added and changed conditions on some parameters</li></ul>				

## Wideband high linearity pre-driver amplifier

Table 12. Revision history...continued

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BTS6302U v.5	20210126	Objective data sheet	-	BTS6302U v.4.1	
modification	changed ESD value on CMD to +/- 500 V				
BTS6302U v.4.1	20201125	Objective data sheet	-	BTS6302U v.4	
modification	added official drawing of the Functional diagram				
BTS6302U v.4	20201120	Objective data sheet	-	BTS6302U v.3	
modification	<ul> <li>removed R16, and C16 from application schematic</li> <li>added condition 4.2 GHz to 5 GHz to G<sub>flat</sub>, and t<sub>d(grp)</sub></li> <li>changed values on some characteristics</li> </ul>				
BTS6302U v.3	20200925	Objective data sheet	-	BTS6302U v.2	
modification	<ul> <li>removed gain mode 2</li> <li>changed T<sub>case</sub> max to 115 °C</li> <li>changed I<sub>CC</sub>, ON state, P<sub>o</sub> = 15 dBm from 92 mA to 100 mA, and ON state, quiescent from 78 mA to 90 mA</li> </ul>				
BTS6302U v.2	20200917	Objective data sheet	-	BTS6302U v.1.1	
modification	<ul><li>changed description of pin 15 to n.c.</li><li>added footprint information</li></ul>				
BTS6302U v.1.1	20200901	Objective data sheet	-	BTS6302U v.1	
modification	added official pin layout, and application diagram				
BTS6302U v.1	20200814	Objective data sheet	-	-	

Wideband high linearity pre-driver amplifier

## 20 Legal information

#### 20.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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**Product data sheet** 

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#### Wideband high linearity pre-driver amplifier

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## Wideband high linearity pre-driver amplifier

### **Contents**

1	General description	1
2	Features and benefits	
3	Applications	1
4	Quick reference data	2
5	Ordering information	2
6	Marking	
7	Functional diagram	3
8	Pinning information	
8.1	Pinning	
8.2	Pin description	
9	Functional description	4
10	Limiting values	5
11	Recommended operating conditions	
12	Thermal characteristics	
13	Characteristics	6
14	Graphs	7
15	Application information	12
16	Package outline	
16.1	Footprint and solder information	14
17	Handling information	
18	Abbreviations	
19	Revision history	
20	Legal information	

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